

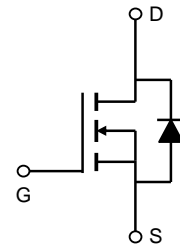
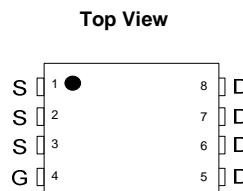
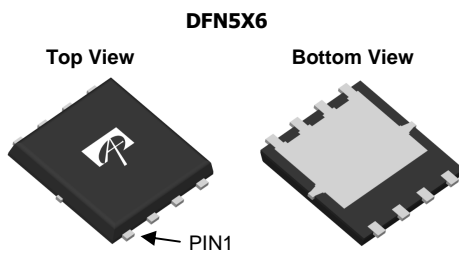
General Description

The AON6408 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is for PWM applications.

Product Summary

V_{DS} (V) = 30V
 I_D = 25A (V_{GS} = 10V)
 $R_{DS(ON)} < 6.5m\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 9.5m\Omega$ (V_{GS} = 4.5V)

100% UIS Tested
100% Rg Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ\text{C}$	25
		$T_C=100^\circ\text{C}$	20
Pulsed Drain Current ^C	I_{DM}	130	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	14.5
		$T_A=70^\circ\text{C}$	11.5
Avalanche Current ^C	I_{AR}	32	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	51	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	31
		$T_C=100^\circ\text{C}$	12.5
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	2.4
		$T_A=70^\circ\text{C}$	1.5
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	17	21	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}				
Maximum Junction-to-Case	$R_{\theta JC}$	3.4	4	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.5	2	2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	130			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$ $T_J=125^\circ\text{C}$		5.4	6.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=20\text{A}$		8.4	10.1	
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$		70		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.75	1	V
I_S	Maximum Body-Diode Continuous Current				31	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$	1270	1590	1900	pF
C_{oss}	Output Capacitance		170	240	310	pF
C_{rss}	Reverse Transfer Capacitance		87	145	200	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	0.8	1.5	2.3	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, I_D=20\text{A}$	24	30	36	nC
$Q_g(4.5\text{V})$	Total Gate Charge		12	15	18	nC
Q_{gs}	Gate Source Charge		4.2	5.2	6.2	nC
Q_{gd}	Gate Drain Charge		4.7	7.8	11	nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, R_L=0.83\Omega,$ $R_{GEN}=3\Omega$		6.7		ns
t_r	Turn-On Rise Time			3.5		ns
$t_{D(off)}$	Turn-Off Delay Time			22.5		ns
t_f	Turn-Off Fall Time			4		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}, di/dt=500\text{A}/\mu\text{s}$	22	28	34	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}, di/dt=500\text{A}/\mu\text{s}$	19	24	30	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

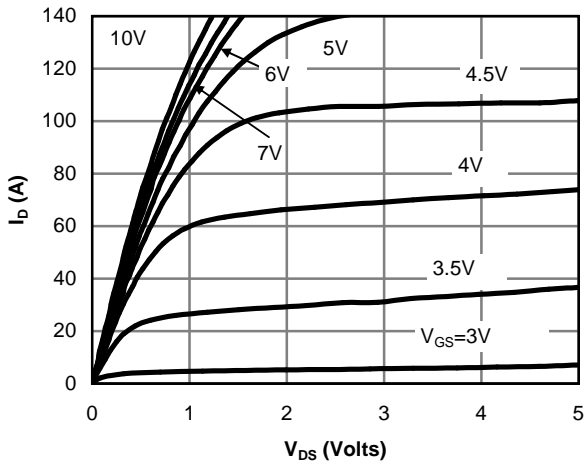


Fig 1: On-Region Characteristics (Note E)

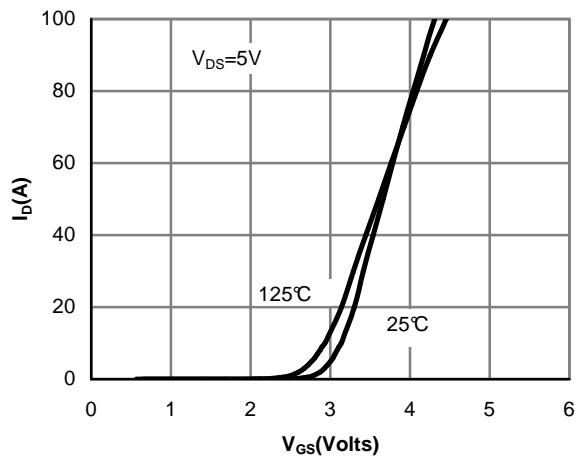


Figure 2: Transfer Characteristics (Note E)

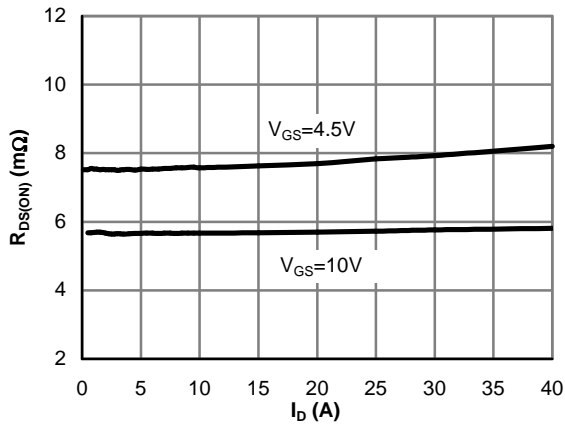


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

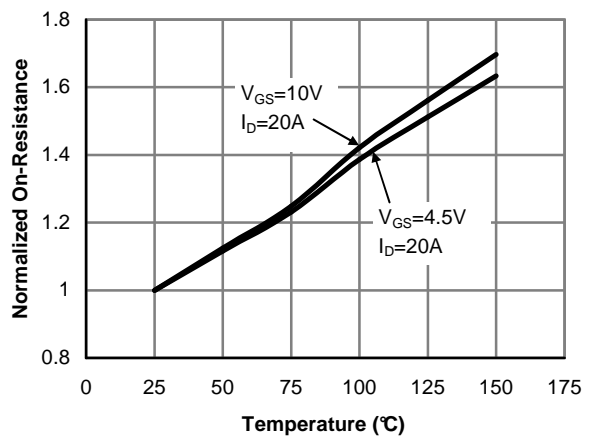


Figure 4: On-Resistance vs. Junction Temperature (Note E)

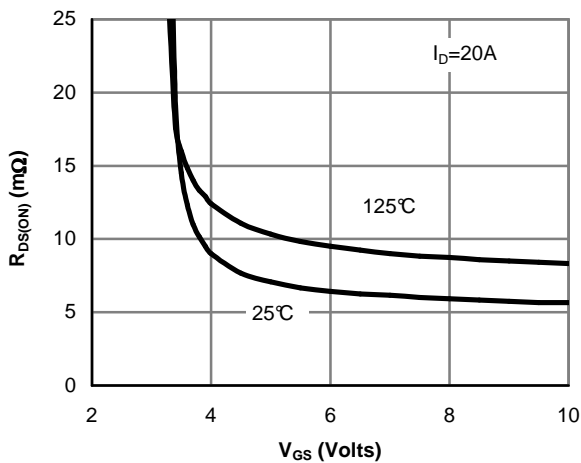


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

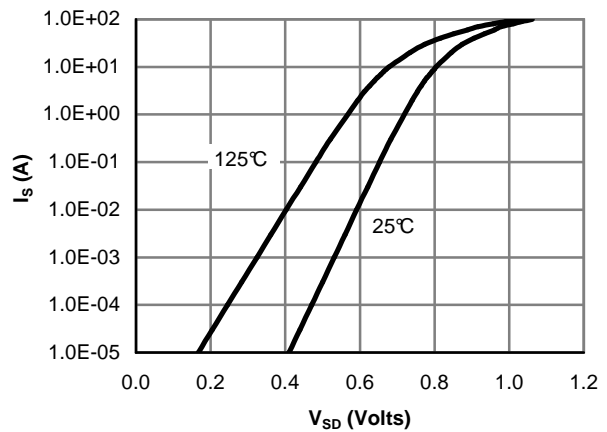


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

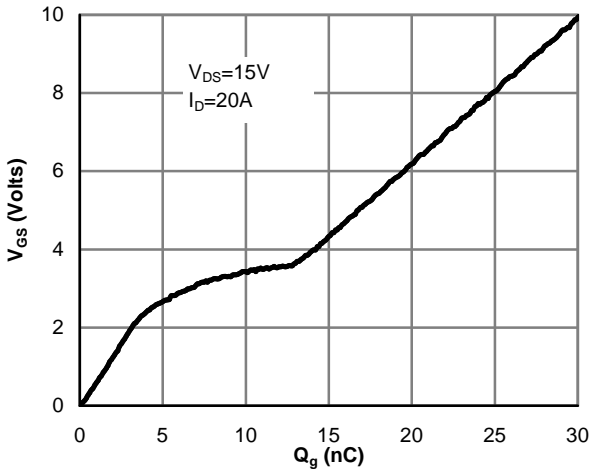


Figure 7: Gate-Charge Characteristics

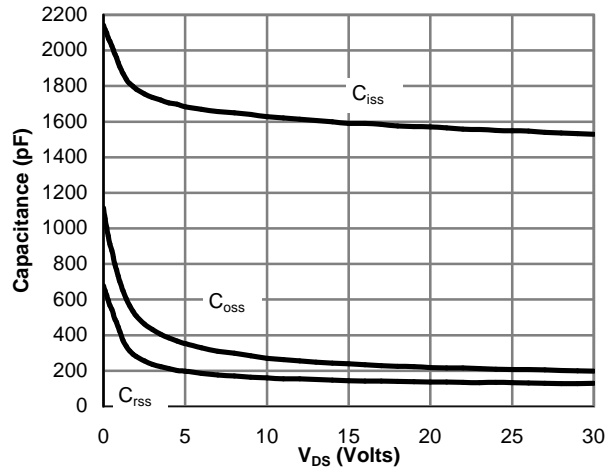


Figure 8: Capacitance Characteristics

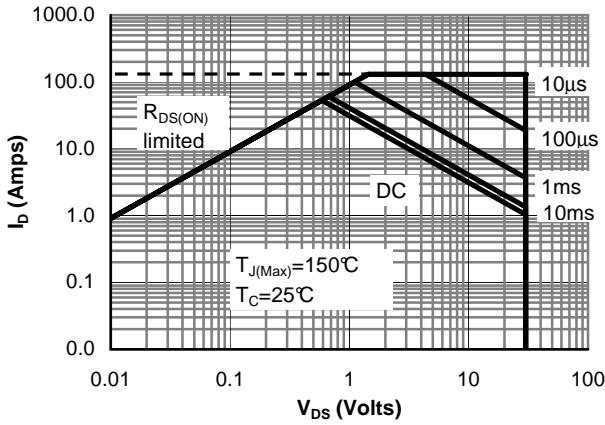


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

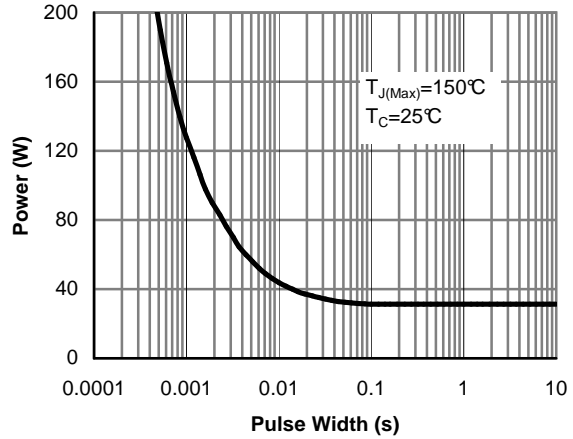


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

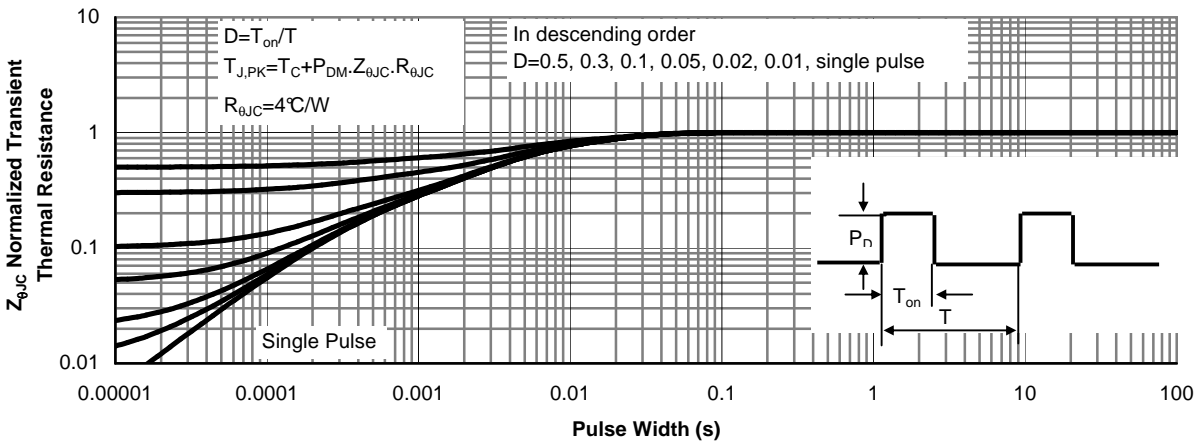


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

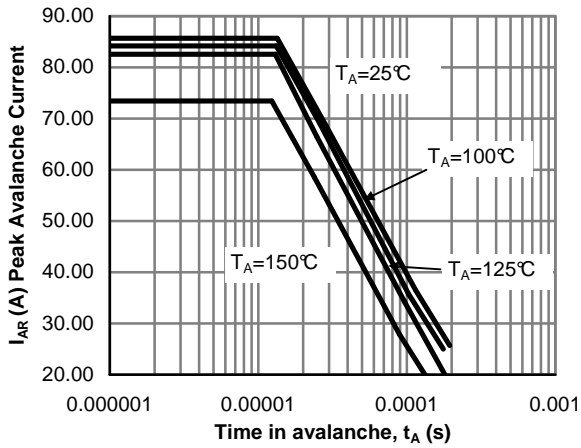


Figure 12: Single Pulse Avalanche capability (Note C)

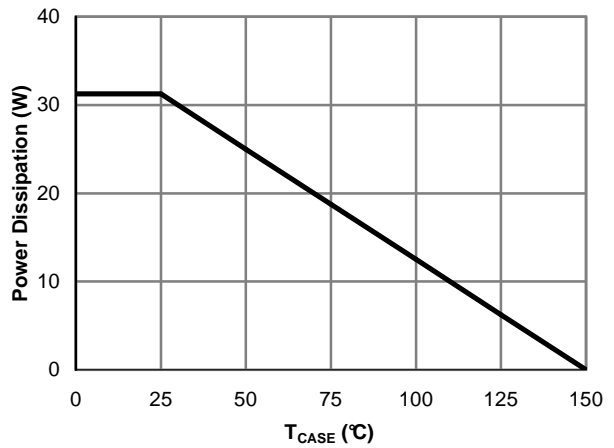


Figure 13: Power De-rating (Note F)

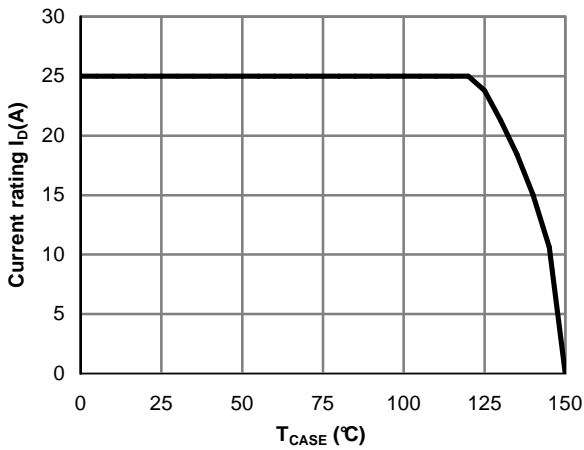


Figure 14: Current De-rating (Note F)

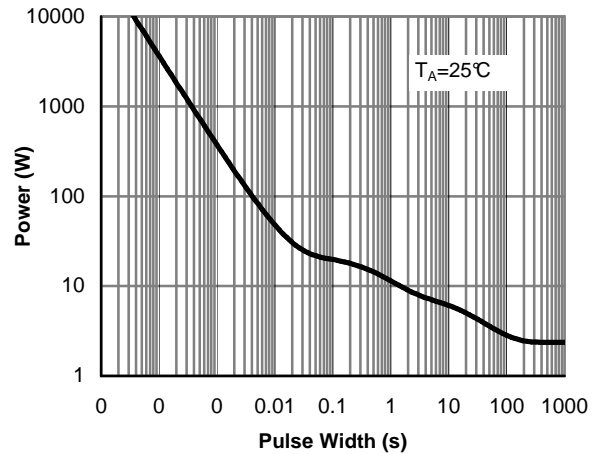


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

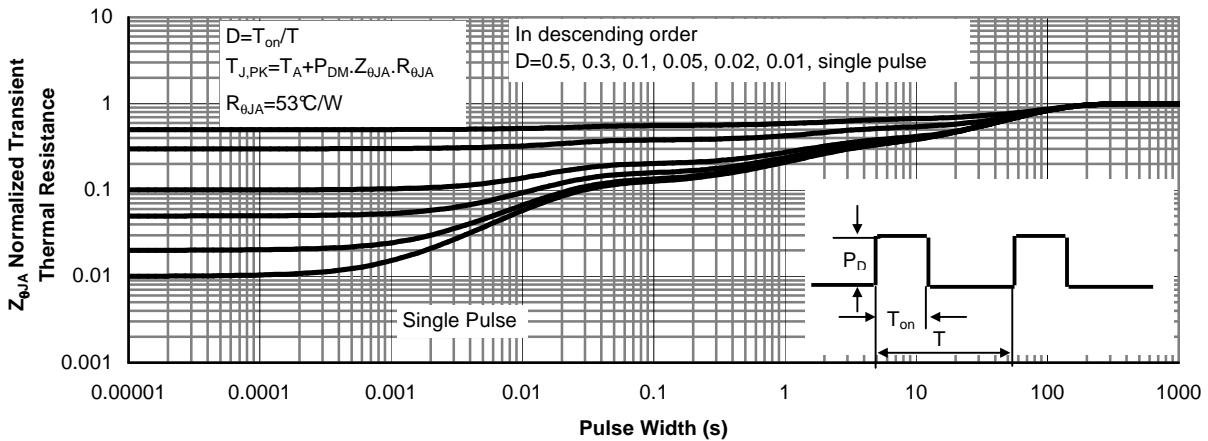
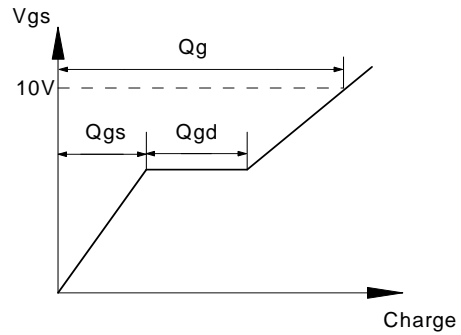
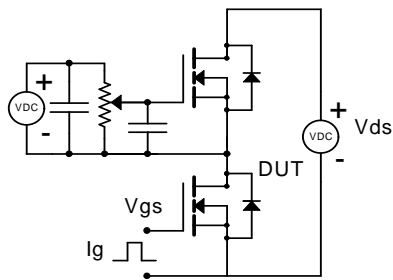
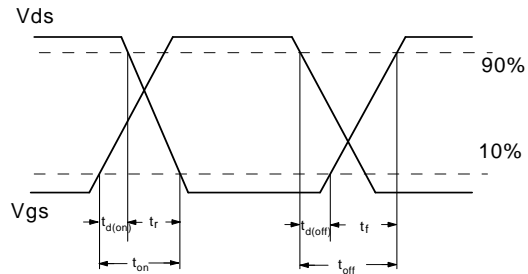
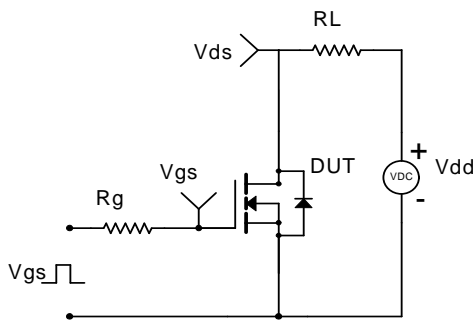


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

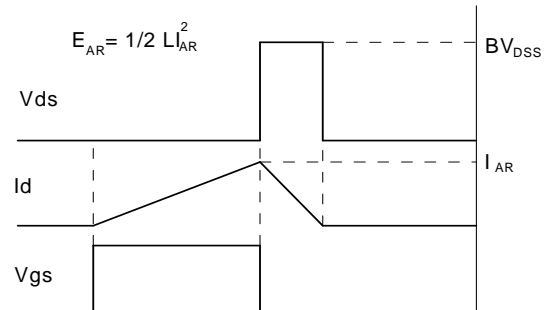
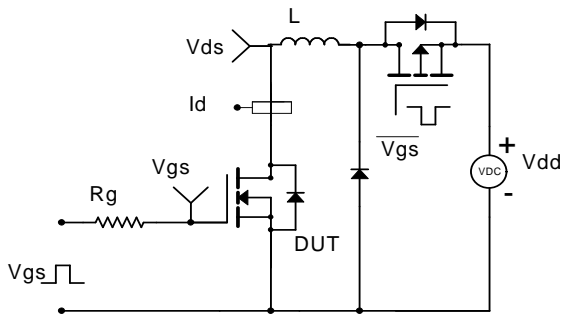
Gate Charge Test Circuit & Waveform



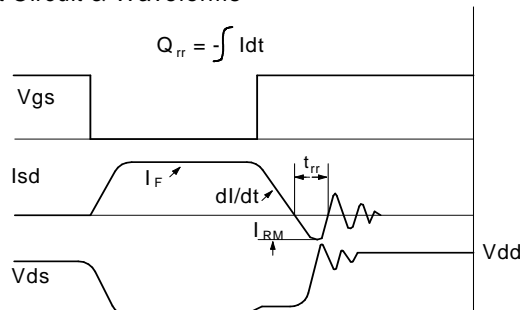
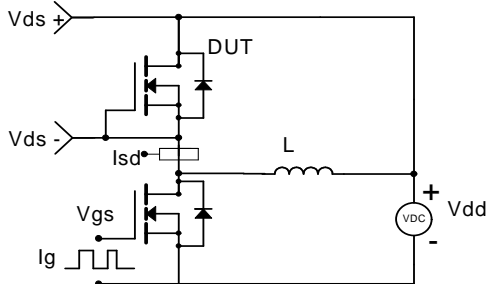
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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